

CLAIMS

1. A polishing composition for use in polishing for forming wiring in a semiconductor device, the polishing composition characterized by containing:
 - 5 colloidal silica,
 - an acid,
 - an anticorrosive,
 - a completely saponified polyvinyl alcohol, and
 - water.
- 10 2. The polishing composition according to Claim 1, characterized by further containing an oxidizing agent.
3. The polishing composition according to Claim 1 or 2, characterized in that the
15 colloidal silica has an average particle size of 0.01 to 0.5 μm .
4. The polishing composition according to any one of Claims 1 to 3, characterized in that the colloidal silica includes a first colloidal silica having an average particle size of 0.05 μm or more and 0.3 μm or less, and a second colloidal silica having an average particle size
20 of 0.01 μm or more and less than 0.05 μm .
5. The polishing composition according to any one of Claims 1 to 4, characterized in that the acid includes at least one kind selected from nitric acid, hydrochloric acid, sulfuric acid, lactic acid, acetic acid, oxalic acid, citric acid, malic acid, succinic acid, butyric acid
25 and malonic acid.
6. A method for polishing an object, the method characterized by using the polishing composition according to any one of Claims 1 to 5 in order to form wiring (17) in a semiconductor device.
30
7. A method for polishing an object to form wiring (17) in a semiconductor device, wherein the object has a barrier layer (14) and a conductive layer (15) in this order on an insulating layer (12) having a trench (13), and the barrier layer and the conductive layer have a portion positioned outside the trench and a portion positioned inside the trench,
35 respectively, the method characterized by:

removing the portion of the conductive layer positioned outside the trench and the portion of the barrier layer positioned outside the trench by chemical mechanical polishing using the polishing composition according to any one of Claims 1 to 5 to expose an upper surface of the insulating layer.

5

8. A method for polishing an object to form wiring (17) in a semiconductor device, wherein the object has a barrier layer (14) and a conductive layer (15) in this order on an insulating layer (12) having a trench (13), and the barrier layer and the conductive layer have a portion positioned outside the trench and a portion positioned inside the trench,

10 respectively, the method characterized by:

removing a part of the portion of the conductive layer positioned outside the trench by chemical mechanical polishing to expose an upper surface of the barrier layer, and

removing the remaining part of the portion of the conductive layer positioned outside the trench and the portion of the barrier layer positioned outside the trench by

15 chemical mechanical polishing to expose an upper surface of the insulating layer,

wherein a first polishing composition is used in the chemical mechanical polishing to remove a part of the portion of the conductive layer positioned outside the trench, and a second polishing composition is used in the chemical mechanical polishing to remove the remaining part of the portion of the conductive layer positioned outside the trench and the portion of the barrier layer positioned outside the trench, and

20

the first polishing composition includes a surfactant, a silicon oxide, a carboxylic acid, an anticorrosive, an oxidizing agent and water, the surfactant including at least one kind selected from the compounds represented by general formulae (1) to (7) and salts thereof;

25

in the general formula (1), R^1 represents an alkyl group having 8 to 16 carbon atoms, R^2 represents a hydrogen atom, a methyl group, or an ethyl group, R^3 represents an alkylene group having 1 to 8 carbon atoms, $-(CH_2CH_2O)_l-$, $-(CH_2CH(CH_3)O)_m-$, or a combination of at least two kinds thereof, when R^3 represents $-(CH_2CH_2O)_l-$ or $-(CH_2CH(CH_3)O)_m-$, l and m are an integer of 1 to 8, when R^3 represents the combination of $-(CH_2CH_2O)_l-$ and $-(CH_2CH(CH_3)O)_m-$, the sum of l and m is an integer of 8 or less, X^1 represents a carboxyl group or a sulfone group;

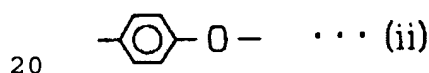
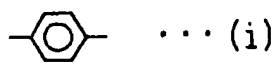
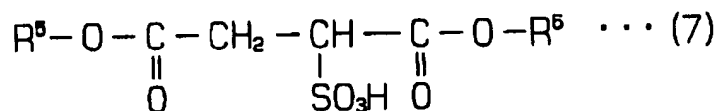
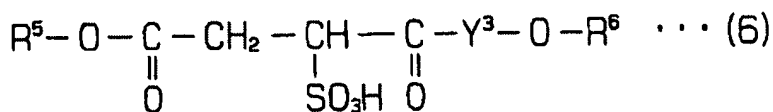
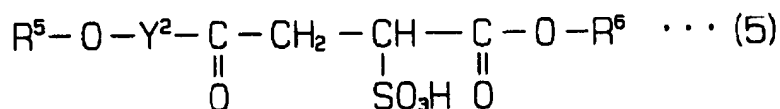
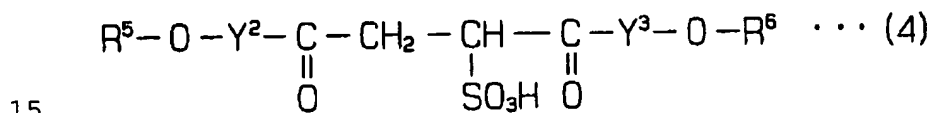
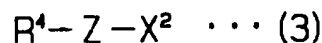
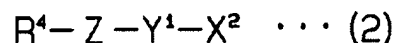
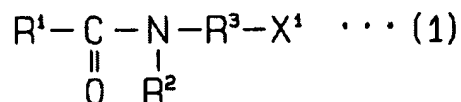
30

in the general formulae (2) and (3), R^4 represents an alkyl group having 8 to 16 carbon atoms, Z is a functional group represented by the chemical formula (i) or (ii), Y^1 represents $-(CH_2CH_2O)_n-$, $-(CH_2CH(CH_3)O)_p-$, or a combination of $-(CH_2CH_2O)_n-$ and $-(CH_2CH(CH_3)O)_p-$, when Y^1 represents $-(CH_2CH_2O)_n-$ or $-(CH_2CH(CH_3)O)_p-$, n and p are an

35

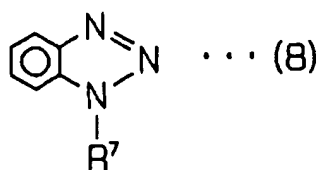
integer of 1 to 6, when Y^1 represents the combination of $-(CH_2CH_2O)_n-$ and $-(CH_2CH(CH_3)O)_p-$, sum of n and p is an integer of 6 or less, X^2 represents a phosphoric acid group or a sulfone group; and

- in the general formulae (4) to (7), each of R^5 and R^6 represents a hydrogen atom, a hydroxyl group, or an alkyl group having 8 to 16 carbon atoms, each of Y^2 and Y^3 represents $-(CH_2CH_2O)_q-$, $-(CH_2CH(CH_3)O)_r-$, or a combination of $-(CH_2CH_2O)_q-$ and $-(CH_2CH(CH_3)O)_r-$, when Y^2 or Y^3 represents $-(CH_2CH_2O)_q-$ or $-(CH_2CH(CH_3)O)_r-$, q and r are an integer of 1 to 6, when Y^2 or Y^3 represents the combination of $-(CH_2CH_2O)_q-$ and $-(CH_2CH(CH_3)O)_r-$, the sum of q and r is an integer of 6 or less, and
- the second polishing composition is the polishing composition according to any one of Claims 1 to 5.



9. The method according to Claim 8, characterized in that the carboxylic acid in the first polishing composition is an α -amino acid.

5 10. The method according to Claim 8 or 9, characterized in that the anticorrosive in the first polishing composition is a benzotriazole derivative represented by general formula (8):



in the general formula (8), R⁷ represents an alkyl group having a carboxyl group, an alkyl group having a hydroxyl group and a tertiary amino group, an alkyl group having a hydroxy group, or an alkyl group other than those.

10

11. A method for polishing an object to form wiring (17) in a semiconductor device, wherein the object has a barrier layer (14) and a conductive layer (15) in this order on an insulating layer (12) having a trench (13), and the barrier layer and the conductive layer have a portion positioned outside the trench and a portion positioned inside the trench, respectively, the method characterized by:

15

removing a part of the portion of the conductive layer positioned outside the trench by chemical mechanical polishing to expose an upper surface of the barrier layer, and

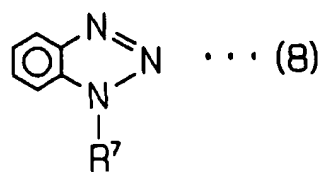
removing the remaining part of the portion of the conductive layer positioned outside the trench and the portion of the barrier layer positioned outside the trench by chemical mechanical polishing to expose an upper surface of the insulating layer,

20

wherein a first polishing composition is used in the chemical mechanical polishing to remove a part of the portion of the conductive layer positioned outside the trench, and a second polishing composition is used in the chemical mechanical polishing to remove the remaining part of the portion of the conductive layer positioned outside the trench and the portion of the barrier layer positioned outside the trench,

25

the first polishing composition includes an α -amino acid, a benzotriazole derivative, a silicon oxide, a surfactant, an oxidizing agent and water, the benzotriazole derivative is represented by general formula (8):



in the general formula (8), R^7 represents an alkyl group having a carboxyl group, an alkyl group having a hydroxyl group and a tertiary amino group, an alkyl group having a hydroxyl group, or an alkyl group other than those, and

5 the second polishing composition is the polishing composition according to any one of Claims 1 to 5.